Amendments to the Claims:

Following is a complete listing of the claims pending in the application, as amended:

- 1. (Currently amended) An image sensor comprising:
- a plurality of pixels formed in a semiconductor substrate, each pixel including a light sensitive element;
- a layer formed over said light sensitive elements;
- a micro-lens over each of said light sensitive elements and directly atop said layer; and
- a trench structure surrounding each of said micro-lenss, said trench structure formed in said layer and extending to the interface between said layer and said micro-lens.
- 2. (Original) The image sensor of Claim 1 wherein said trench structure is circular.
- 3. (Original) The image sensor of Claim 1 wherein said trench structure has a rectangular cross-section.
- 4. (Original) The image sensor of Claim 1 wherein the micro-lenss are formed from polymethylmethacrylate (PMMA) or polyglycidylmethacrylate (PGMA).
 - 5. (Currently amended) An image sensor comprising:
 - a plurality of pixels formed in a semiconductor substrate, each pixel including a light sensitive element;
 - a micro-lens over each of said light sensitive elements; and
- a trench structure surrounding each of said micro-lenss, The image sensor of Claim 1 wherein said trench structure has a depth on the order of 0.2 microns.

- 6. (Cancelled).
- 7. (Original) The image sensor of Claim 1 further including a color filter layer between said micro-lenss and said light sensitive elements.
 - 8. (Currently amended) A pixel of an image sensor comprising:
 - a light sensitive element formed in a semiconductor substrate;
 - a layer formed over said light sensitive element;
 - a micro-lens over said light sensitive element and directly atop said layer; and
 - a trench structure surrounding said micro-lens, said trench structure formed in said layer and extending to the interface between said layer and said micro-lens.
 - 9. (Original) The pixel of Claim 8 wherein said trench structure is circular.
- 10. (Original) The pixel of Claim 8 wherein said trench structure has a rectangular cross-section.
- 11. (Original) The pixel of Claim 8 wherein the micro-lens is formed from polymethylmethacrylate (PMMA) or polyglycidylmethacrylate (PGMA).
 - 12. (Currently amended) A pixel of an image sensor comprising:
 - a light sensitive element formed in a semiconductor substrate;
 - a micro-lens over said light sensitive element; and
- a trench structure surrounding said micro-lens, The pixel of Claim 8 wherein said trench structure has a depth on the order of 0.2 microns.
 - 13. (Cancelled).

- 14. (Original) The pixel of Claim 8 further including a color filter layer between said microlenss and said light sensitive elements.
 - 15. 19. (Cancelled)